

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-20 (Canceled).

Claim 21 (Previously Presented): A semiconductor device comprising:

a first semiconductor layer formed on a semiconductor substrate with one of an insulating film and a cavity interposed between said semiconductor substrate and said first semiconductor layer, said first semiconductor layer having a shape different than a rectangle; and

a second semiconductor layer having a rim portion formed on an outerperipheral of said semiconductor substrate, said rim portion of said second semiconductor layer surrounding said first semiconductor layer, said second semiconductor layer further having a rectangular portion, and said rectangular portion of said second semiconductor layer and said first semiconductor layer having together the shape of a rectangle.

Claim 22 (Original): A semiconductor device according to claim 21, wherein the area of said second semiconductor layer is larger than the area of said first semiconductor layer.

Claim 23 (Original): A semiconductor device according to claim 21, wherein said second semiconductor layer is deposited by epitaxial growth.

Claims 24-32 (Canceled).